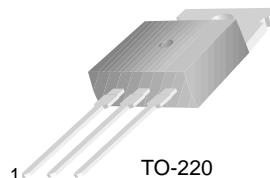


# KSC2335

KSC2335

## High Speed, High Voltage Switching

- Industrial Use



TO-220  
1.Base 2.Collector 3.Emitter

## NPN Epitaxial Silicon Transistor

### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	7	A
$I_{CP}$	*Collector Current (Pulse)	15	A
$I_B$	Base Current (DC)	3.5	A
$P_C$	Collector Dissipation ( $T_a=25^\circ\text{C}$ )	1.5	W
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

\*  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 10\%$

### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 3A, I_{B1} = 0.6A, L = 1mH$	400		V
$V_{CEX(sus)1}$	Collector-Emitter Sustaining Voltage	$I_C = 3A, I_{B1} = -I_{B2} = 0.6A$ $V_{BE(off)} = -5V, L = 180\mu H, \text{Clamped}$	450		V
$V_{CEX(sus)2}$	Collector-Emitter Sustaining Voltage	$I_C = 6A, I_{B1} = 2A, I_{B2} = -0.6A$ $V_{BE(off)} = -5V, L = 180\mu H, \text{Clamped}$	400		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 400V, I_E = 0$		10	$\mu\text{A}$
$I_{CER}$	Collector Cut-off Current	$V_{CE} = 400V, R_{BE} = 51\Omega @ T_C = 125^\circ\text{C}$		1	mA
$I_{CEX1}$	Collector Cut-off Current	$V_{CE} = 400V, V_{BE(off)} = -1.5V$		10	$\mu\text{A}$
$I_{CEX2}$	Collector Cut-off Current	$V_{CE} = 400V, V_{BE(off)} = -1.5V @ T_C = 125^\circ\text{C}$		1	mA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5V, I_C = 0$		10	$\mu\text{A}$
$h_{FE1}$	* DC Current Gain	$V_{CE} = 5V, I_C = 0.1A$	20	80	
$h_{FE2}$		$V_{CE} = 5V, I_C = 1A$	20	80	
$h_{FE3}$		$V_{CE} = 5V, I_C = 3A$	10		
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$		1	V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$		1.2	V
$t_{ON}$	Turn ON Time	$V_{CC} = 150V, I_C = 3A$ $I_{B1} = -I_{B2} = 0.6A$ $R_L = 50\Omega$		1	$\mu\text{s}$
$t_{STG}$	Storage Time			2.5	$\mu\text{s}$
$t_F$	Fall Time			1	$\mu\text{s}$

\* Pulse Test:  $PW \leq 350\mu\text{s}$ , Duty Cycle  $\leq 2\%$  Pulsed

## $h_{FE}$ Classification

Classification	R	O	Y
$h_{FE2}$	20 ~ 40	30 ~ 60	40 ~ 80

# Typical Characteristics

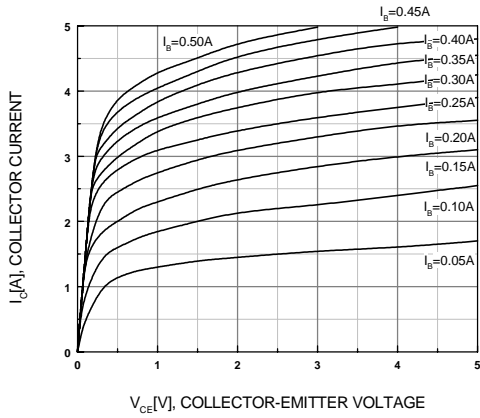


Figure 1. Static Characteristic

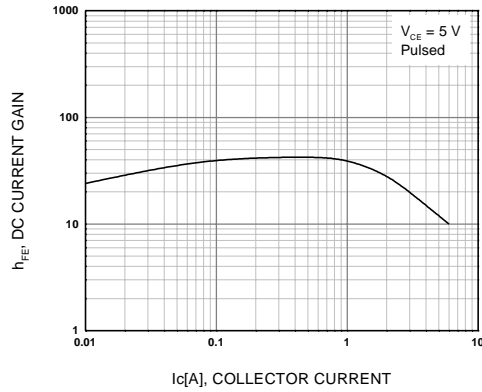


Figure 2. DC current Gain

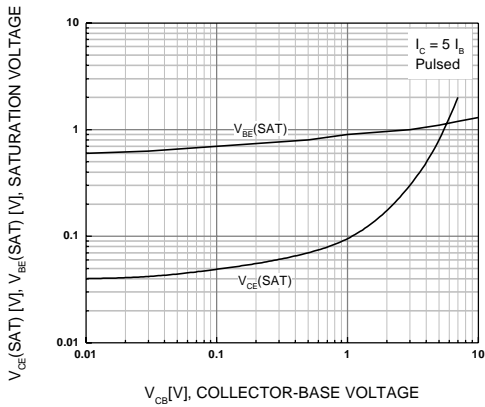


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

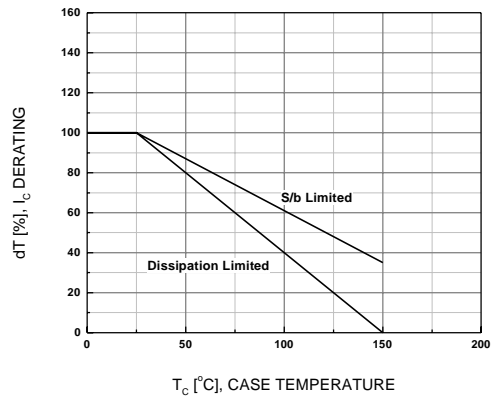


Figure 4. Derating Curve of Safe Operating Areas

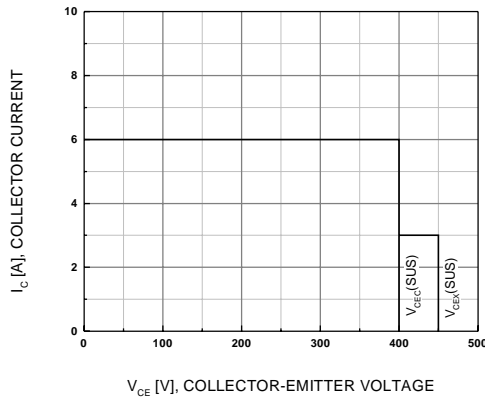


Figure 5. Reverse Bias Safe Operating Area

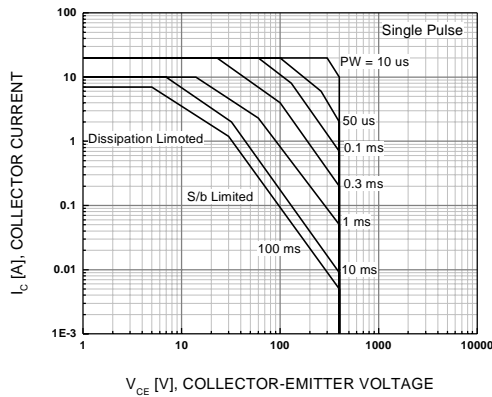
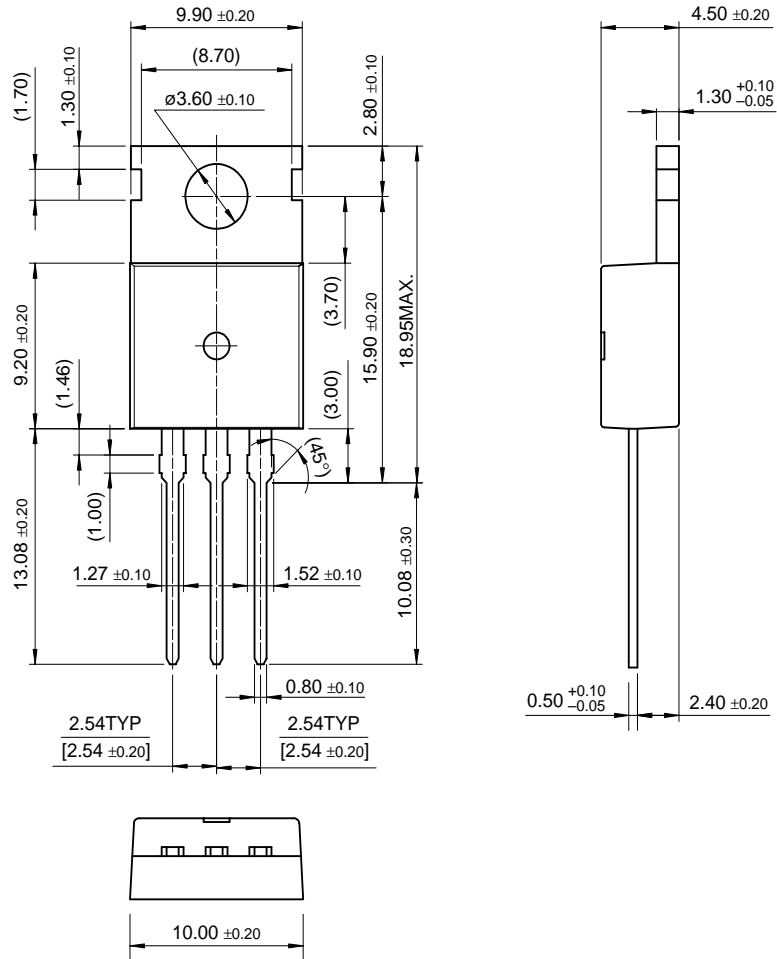


Figure 6. Forward Bias Safe Operating Area

# Package Dimensions

KSC2335

## TO-220



Dimensions in Millimeters

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	OPTOPLANAR™	STAR*POWER™
Bottomless™	FASTr™	PACMAN™	Stealth™
CoolFET™	FRFET™	POP™	SuperSOT™-3
CROSSVOLT™	GlobalOptoisolator™	Power247™	SuperSOT™-6
DenseTrench™	GTO™	PowerTrench®	SuperSOT™-8
DOMET™	HiSeC™	QFET™	SyncFET™
EcoSPARK™	ISOPLANAR™	QS™	TruTranslation™
E <sup>2</sup> CMOS™	LittleFET™	QT Optoelectronics™	TinyLogic™
EnSigna™	MicroFET™	Quiet Series™	UHC™
FACT™	MICROWIRE™	SLIENT SWITCHER®	UltraFET®
FACT Quiet Series™	OPTOLOGIC™	SMART START™	VCX™

STAR\*POWER is used under license

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Fairchild Semiconductor

SEARCH | [Parametric](#) | [Cross Reference](#)

[space](#)

[Product Folders and](#)

[Applies](#)

[find products](#)

[Home](#) >> [Find products](#) >>

[Products groups](#)

[Analog and Mixed](#)

[Signal](#)

[Discrete](#)

[Interface](#)

[Logic](#)

[Microcontrollers](#)

[Non-Volatile](#)

[Memory](#)

[Optoelectronics](#)

[Markets and](#)

[applications](#)

[New products](#)

[Product selection and](#)

[parametric search](#)

[Cross-reference](#)

[search](#)

KSC2335  
NPN Epitaxial Silicon Transistor

Contents

[Features](#) | [Applications](#) | [Product status/pricing/packaging](#)

Features

- Industrial Use

[back to top](#)

Applications

**High Speed, High Voltage Switching**

[back to top](#)

Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC2335YTU	Full Production	\$0.495	TO-220	3	RAIL
KSC2335R	Full Production	\$0.495	TO-220	3	BULK
KSC2335O	Full Production	\$0.495	TO-220	3	BULK
KSC2335RTU	Full Production	\$0.495	TO-220	3	RAIL
KSC2335OTU	Full Production	\$0.495	TO-220	3	RAIL
KSC2335Y	Full Production	\$0.495	TO-220	3	BULK

\* 1,000 piece Budgetary Pricing

[back to top](#)

[Home](#) | [Find products](#) | [Technical information](#) | [Buy products](#) | [Support](#) | [Company](#) | [Contact us](#) | [Site index](#) | [Privacy policy](#)

Related Links

[Request samples](#)

[How to order products](#)

[Product Change Notices \(PCNs\)](#)

[Support](#)

[Distributor and field sales representatives](#)

[Quality and reliability](#)

[Design tools](#)

Datasheet

[Download this datasheet](#)

PDF

[e-mail this datasheet](#)

[E-]

This page [Print version](#)

